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**(71) Applicant(s):**

VISHAY GENERAL SEMICONDUCTOR LLC [US/US]; 100 Motor Parkway, Suite 135 Hauppauge, New York 11788 (US) *(for all designated states except US)*

WANG, Benson [\*\*/\*\*]; 2F, No. 6, Alley 9, Lane 143 Anle Road, Jhonghe City Taipei (TW) *(for US only)*

LU, Kevin [\*\*/\*\*]; 19, Alley 3, Lane 151 Hersto Street, Fongyuan Taichung, Taipei (TW) *(for US only)*

CHIANG, Warren [\*\*/\*\*]; No. 6, 5F, 265 Lane, Kang-Ning Road Section III, Nei-Hu Taipei (TW) *(for US only)*

CHEN, Max [\*\*/\*\*]; 17F, No. 10, Sec. 4 Huang-Her East Road Young-her Taipei (TW) *(for US only)*

**(72) Inventor(s):**

WANG, Benson; 2F, No. 6, Alley 9, Lane 143 Anle Road, Jhonghe City Taipei (TW)

LU, Kevin; 19, Alley 3, Lane 151 Hersto Street, Fongyuan Taichung, Taipei (TW)

CHIANG, Warren; No. 6, 5F, 265 Lane, Kang-Ning Road Section III, Nei-Hu Taipei (TW)

CHEN, Max; 17F, No. 10, Sec. 4 Huang-Her East Road Young-her Taipei (TW)

**(74) Agent(s):**

MAYER, Stuart, H.; Mayer & Williams PC 251 North Avenue West, 2nd Floor Westfield, New Jersey 07090 (US)

**(54) Title (EN):** PROCESS FOR FORMING A PLANAR DIODE USING ONE MASK

**(54) Title (FR):** PROCEDE DE FORMATION D'UNE DIODE PLANE AU MOYEN D'UN MASQUE

**(57) Abstract:**

**(EN):** A planar diode and method of making the same employing only one mask. The diode is formed by coating a substrate with an oxide, removing a central portion of the oxide to define a window through which dopants are diffused. The substrate is given a Ni/Au plating to provide ohmic contact surfaces, and the oxide on the periphery of the window is coated with a polyimide passivating agent overlying the P/N junction.

**(FR):** Diode plane et son procédé de fabrication à l'aide d'un seul masque. Cette diode est formée par enduction d'un substrat d'un oxyde, par enlèvement d'une partie centrale de l'oxyde pour définir une fenêtre par laquelle des dopants sont diffusés. Le substrat subit ensuite un placage de Ni/Au afin que des surfaces de contact ohmique soient produites, et l'oxyde se trouvant sur la périphérie de la fenêtre est enduit d'un agent de passivation au polyimide recouvrant la jonction PN.

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